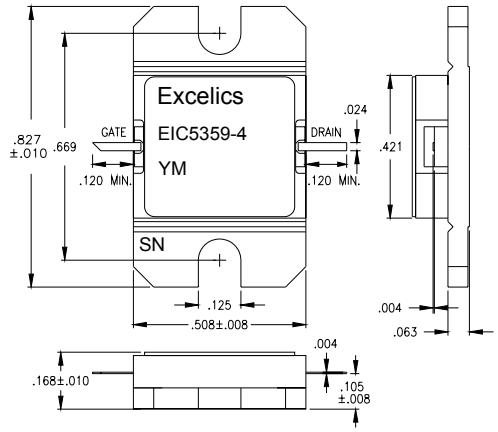
EIC5359-4

ISSUED 5/15/2006

5.3-5.9 GHz 4-Watt Internally Matched Power FET

FEATURES

- **5.3– 5.9GHz Bandwidth**
- **Input/Output Impedance Matched to 50 Ohms**
- **+36.5 dBm Output Power at 1dB Compression**
- **10.5 dB Power Gain at 1dB Compression**
- **34% Power Added Efficiency**
- **Hermetic Metal Flange Package**



ELECTRICAL CHARACTERISTICS (T_a = 25°C)

Caution! ESD sensitive device.

SYMBOL	PARAMETERS/TEST CONDITIONS[1]	MIN	TYP	MAX	UNITS
P_{1dB}	Output Power at 1dB Compression f = 5.3-5.9GHz V_{DS} = 10 V, I_{DSQ} ≈ 1100mA	35.5	36.5		dBm
G_{1dB}	Gain at 1dB Compression f = 5.3-5.9GHz V_{DS} = 10 V, I_{DSQ} ≈ 1100mA	9.5	10.5		dB
ΔG	Gain Flatness f = 5.3-5.9GHz V_{DS} = 10 V, I_{DSQ} ≈ 1100mA			±0.6	dB
PAE	Power Added Efficiency at 1dB Compression V_{DS} = 10 V, I_{DSQ} ≈ 1100mA f = 5.3-5.9GHz		34		%
Id_{1dB}	Drain Current at 1dB Compression f = 5.3-5.9GHz		1200	1400	mA
IM3	Output 3rd Order Intermodulation Distortion Δf=10MHz 2-Tone Test. Pout=25.5 dBm S.C.L Vds = 10 V, I_{DSQ} ≈ 65% I_{DSS} f = 5.9GHz	-43	-46		dBc
I_{DSS}	Saturated Drain Current V_{DS} = 3 V, V_{GS} = 0 V		2000	2500	mA
V_P	Pinch-off Voltage V_{DS} = 3 V, I_{DS} = 20 mA		-2.5	-4.0	V
R_{TH}	Thermal Resistance[3]		5.5	6	°C/W

Note: 1) Tested with 100 Ohm gate resistor. 2) S.C.L. = Single Carrier Level. 3) Overall Rth depends on case mounting.

ABSOLUTE MAXIMUM RATING[1,2]

SYMBOLS	PARAMETERS	ABSOLUTE[1]	CONTINUOUS[2]
Vds	Drain-Source Voltage	15	10V
Vgs	Gate-Source Voltage	-5	-4V
Igsf	Forward Gate Current	43.2mA	14.4mA
Igsr	Reserve Gate Current	-7.2mA	-2.4mA
Pin	Input Power	35.5dBm	@ 3dB Compression
Tch	Channel Temperature	175 °C	175 °C
Tstg	Storage Temperature	-65 to +175 °C	-65 to +175 °C
Pt	Total Power Dissipation	25W	25W

Note: 1. Exceeding any of the above ratings may result in permanent damage.
2. Exceeding any of the above ratings may reduce MTTF below design goals.